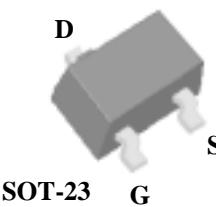




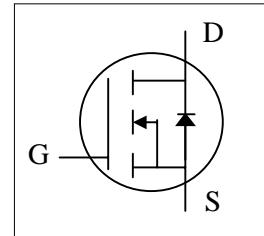
- ▼ Capable of 2.5V gate drive
- ▼ Small package outline
- ▼ Surface mount package



$BV_{DSS}$	20V
$R_{DS(ON)}$	85mΩ
$I_D$	3.2A

## Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current <sup>3</sup> , $V_{GS} @ 4.5V$	3.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current <sup>3</sup> , $V_{GS} @ 4.5V$	2.6	A
$I_{DM}$	Pulsed Drain Current <sup>1,2</sup>	10	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	1.38	W
	Linear Derating Factor	0.01	W/°C
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient <sup>3</sup>	Max.	°C/W



## Electrical Characteristics@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	20	-	-	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_{\text{D}}=1\text{mA}$	-	0.1	-	$\text{V}/^\circ\text{C}$
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=3.6\text{A}$	-	-	85	$\text{m}\Omega$
		$V_{\text{GS}}=2.5\text{V}, I_{\text{D}}=3.1\text{A}$	-	-	115	$\text{m}\Omega$
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.5	-	1.2	V
$g_{\text{fs}}$	Forward Transconductance	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=3.6\text{A}$	-	6	-	S
$I_{\text{DSS}}$	Drain-Source Leakage Current ( $T_j=25^\circ\text{C}$ )	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
	Drain-Source Leakage Current ( $T_j=70^\circ\text{C}$ )	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	10	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Source Leakage	$V_{\text{GS}}=\pm 12\text{V}$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_{\text{D}}=3.6\text{A}$	-	4.4	-	nC
$Q_{\text{gs}}$	Gate-Source Charge		-	0.6	-	nC
$Q_{\text{gd}}$	Gate-Drain ("Miller") Charge		-	1.9	-	nC
$t_{\text{d}(\text{on})}$	Turn-on Delay Time <sup>2</sup>	$V_{\text{DS}}=10\text{V}$	-	5.2	-	ns
$t_r$	Rise Time	$I_{\text{D}}=3.6\text{A}$	-	37	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time	$R_G=6\Omega, V_{\text{GS}}=5\text{V}$	-	15	-	ns
$t_f$	Fall Time	$R_D=2.8\Omega$	-	5.7	-	ns
$C_{\text{iss}}$	Input Capacitance	$V_{\text{GS}}=0\text{V}$	-	145	-	pF
$C_{\text{oss}}$	Output Capacitance	$V_{\text{DS}}=10\text{V}$	-	100	-	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance	f=1.0MHz	-	50	-	pF

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$I_s$	Continuous Source Current ( Body Diode )	$V_D=V_G=0\text{V}, V_S=1.2\text{V}$	-	-	1	A
$I_{\text{SM}}$	Pulsed Source Current ( Body Diode ) <sup>1</sup>		-	-	10	A
$V_{\text{SD}}$	Forward On Voltage <sup>2</sup>	$I_s=1.6\text{A}, V_{\text{GS}}=0\text{V}$	-	-	1.2	V

## Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width  $\leq 300\text{us}$  , duty cycle  $\leq 2\%$ .
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board ;  $270^\circ\text{C}/\text{W}$  when mounted on min. copper pad.

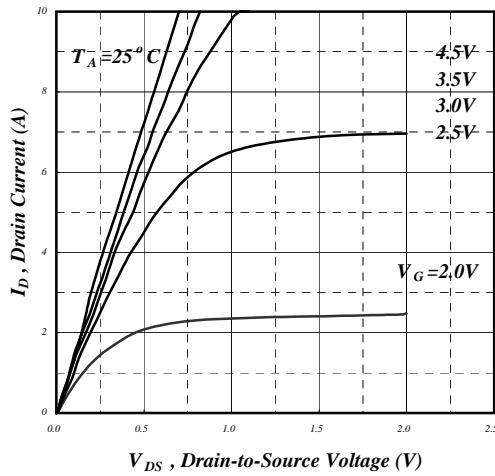


Fig 1. Typical Output Characteristics

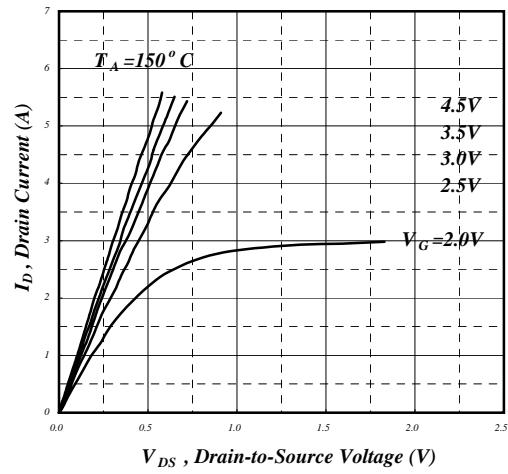


Fig 2. Typical Output Characteristics

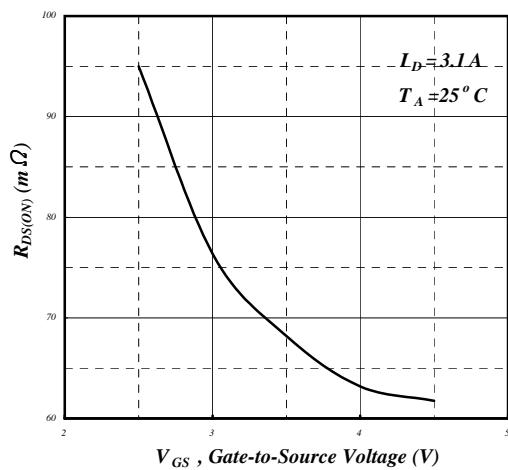


Fig 3. On-Resistance v.s. Gate Voltage

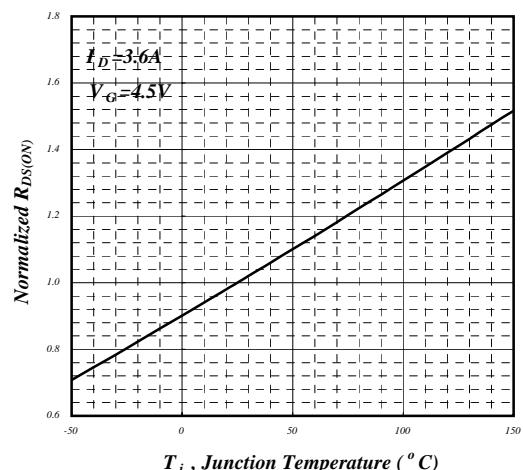


Fig 4. Normalized On-Resistance

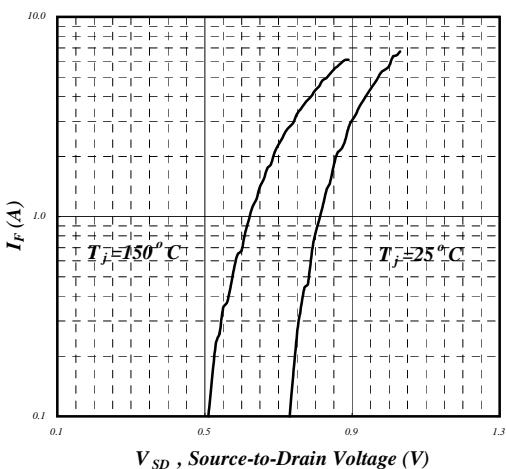


Fig 5. Forward Characteristic of Reverse Diode

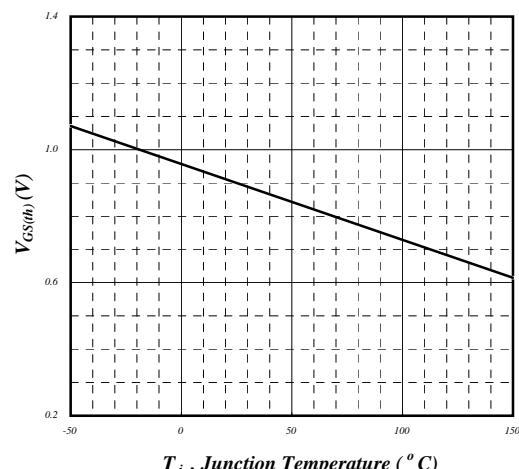
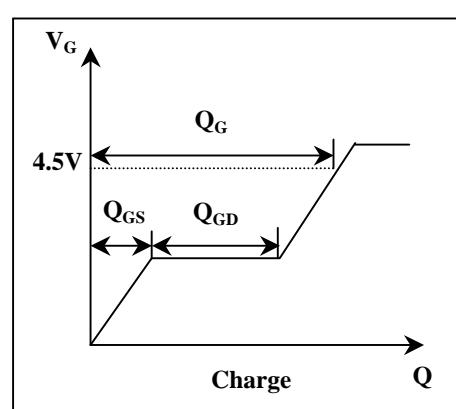
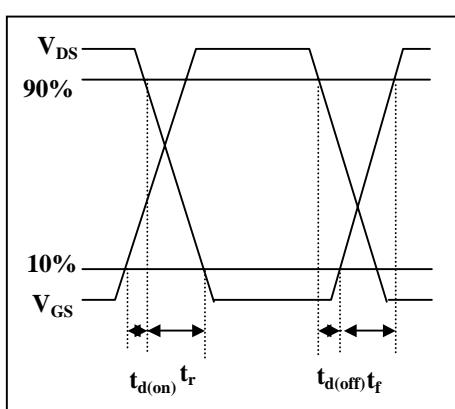
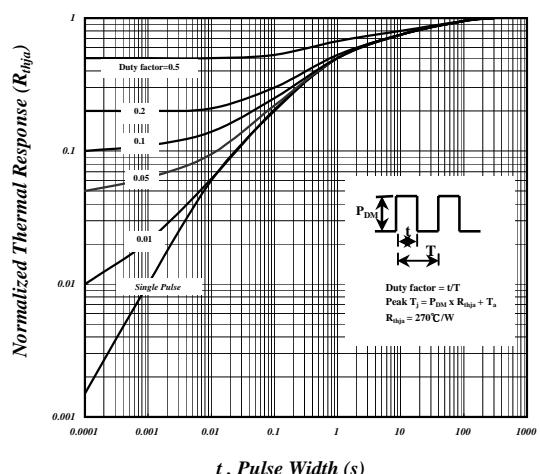
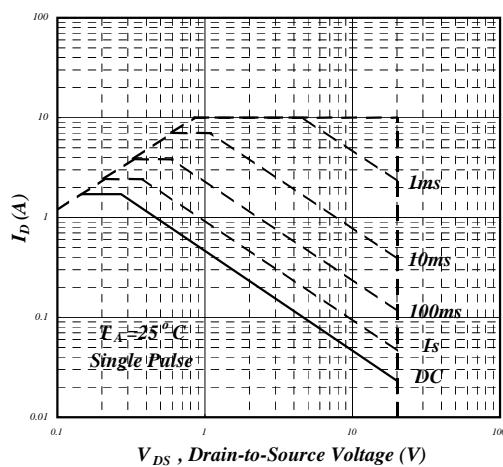
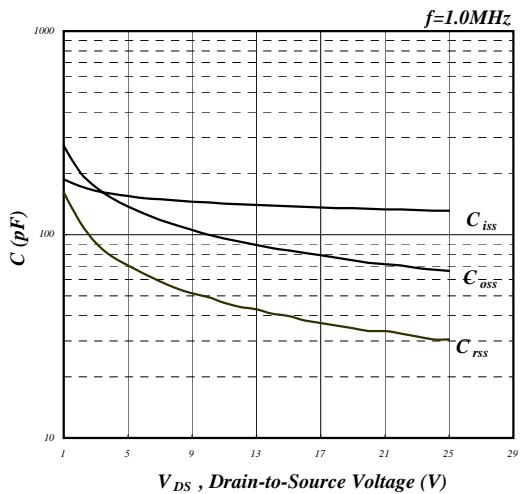
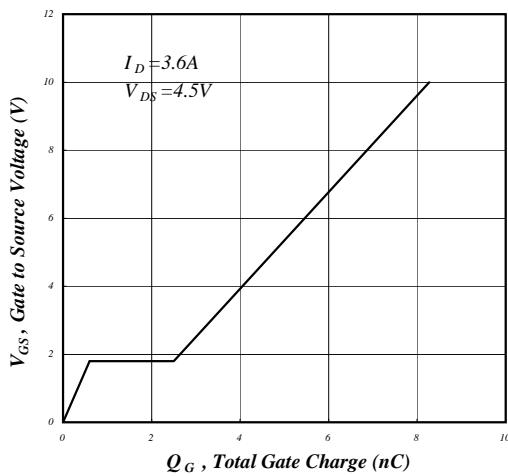


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

# AP2302GN



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